

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

DECLARATION FOR PATENT APPLICATION

As a below named inventor, I hereby declare that:

My residence, post office address and citizenship are as stated below next to my name.

I believe I am an original, first and joint inventor of the subject matter which is claimed and for which a patent is sought on the invention entitled:

IMPROVED MEMORY CELL CAPACITOR STRUCTURE AND
METHOD OF FORMATION

The specification of which is attached hereto.

I hereby state that I have reviewed and understand the contents of the above identified specification, including the claims, as amended by an amendment, if any, specifically referred to in this oath or declaration.

I acknowledge the duty to disclose all information known to me which is material to patentability as defined in Title 37, Code of Federal Regulations, § 1.56.

I hereby claim foreign priority benefits under Title 35, United States Code § 119/365 of any foreign application(s) for patent or inventor's certificate listed below and have also identified below any foreign application for patent or inventor's certificate having a filing date before that of the application on which priority is claimed:

NONE

I hereby claim the benefit under Title 35, United States Code, § 120/365 of any United States and PCT international application(s) listed below and, insofar as the subject matter of each of the claims of this application is not disclosed in the prior United States application in the manner provided by the first paragraph of Title 35, United States Code, § 112, I acknowledge the duty to disclose all information known to me to be material to patentability as defined in Title 37, Code of Federal Regulations, § 1.56(a) which became available between the filing date of the prior application and the national or PCT international filing date of this application:

NONE

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

Please address all correspondence to Thomas J. D'Amico of Dickstein Shapiro Morin & Oshinsky LLP located at 2101 L Street NW

Washington, DC 20037-1526. Telephone calls should be made to (202) 785-9700.

Full name of first inventor: Sam Yang

Inventor's signature:



Date: 5/26/00

Residence: Boise, ID

Citizenship: China

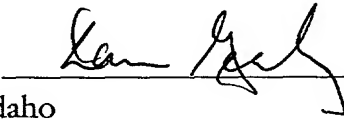
Post Office Address: 5923 S. Sweet Gum Way
Boise, ID 83716

1141089 v1: _GGX011.DOC

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE
DECLARATION FOR PATENT APPLICATION

Signature Page for Second Inventor

Full name of second inventor: Dan Gealy

Inventor's signature:  Date: 6/1/2000

Residence: Kuna, Idaho

Citizenship: United States of America

Post Office Address: 4300 Junayo Lane
Kuna, Idaho 83634

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Sam Yang et al.

Serial No.: Not Yet Assigned

Group Art Unit: Not Yet Assigned

Filed: Concurrently Herewith

Examiner: Not Yet Assigned

For: IMPROVED MEMORY CELL
CAPACITOR STRUCTURE
AND METHOD OF
FORMATION

Assistant Commissioner for Patents
Washington, D.C. 20231

**POWER OF ATTORNEY BY ASSIGNEE AND
CERTIFICATE BY ASSIGNEE UNDER 37 CFR § 3.73(b)**


Micron Technology, Inc., Assignee of the entire right, title and interest in the above-identified application by virtue of the Assignment attached hereto (which is also being submitted concurrently for recordation), hereby appoints the attorneys and agents of the firm of Dickstein Shapiro Morin & Oshinsky, LLP located at 2101 L Street, N.W., Washington, D.C. 20037, listed as follows: Gary M. Hoffman, 26,411; Thomas J. D'Amico, 28,371; Donald A. Gregory, 28,954; James W. Brady Jr., 32,115; Jon D. Grossman, 32,699; Mark J. Thronson, 33,082; Jeremy A. Cubert, 40,399; Laurence E. Fisher, 37,131; Brian A. Lemm, 43,748; John F. Levis, 34,210; Gianni Minutoli, 41,198; Edwin Oh, P-45,319; Eric Oliver, 35,307; William E. Powell III, 39,803; Paul L. Ratcliffe, 45,290; Mark E. Strickland, 45,138 and Salvatore P. Tamburo, P-45,153, and also attorneys of Micron Technology, Inc. as its attorneys with full power of substitution to prosecute this application and to transact all business in the Patent and Trademark Office in connection therewith.

The Assignee certifies that the above-identified assignment has been reviewed and to the best of the Assignee's knowledge and belief, title is in the assignee.

Please direct all correspondence regarding this application to the following:

Dickstein Shapiro Morin & Oshinsky LLP
2101 L Street NW
Telephone: (202) 785-9700
Fax: (202) 887-0689

MICRON TECHNOLOGY,



Michael L. Lynch
Chief Patent Counsel
Registration No. 30,871

Dated: 6-1-2000

ASSIGNMENT AND AGREEMENT

COPY

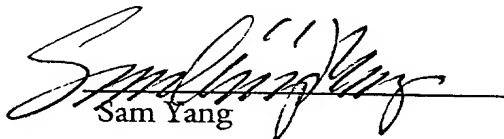
For value received, we, Sam Yang and Dan Gealy, hereby sell, assign and transfer to Micron Technology, Inc., a corporation of the State of Delaware, having an office at 8000 S. Federal Way, Boise, Idaho 83706-9632, U.S.A., and its successors, assigns and legal representatives, the entire right, title and interest, for the United States of America, in and to certain inventions related to an invention entitled IMPROVED MEMORY CELL CAPACITOR STRUCTURE AND METHOD OF FORMATION, described in an application for Letters Patent of the United States, executed by us of even date herewith, and all the rights and privileges in said application and under any and all Letters Patent that may be granted in the United States for said inventions; and we also concurrently hereby sell, assign and transfer to Micron Technology, Inc. the entire right, title and interest in and to said inventions for all countries foreign to the United States, including all rights of priority arising from the application aforesaid, and all the rights and privileges under any and all forms of protection, including Letters Patent, that may be granted in said countries foreign to the United States for said inventions.

We authorize Micron Technology, Inc. to make application for such protection in its own name and maintain such protection in any and all countries foreign to the United States, and to invoke and claim for any application for patent or other form of protection for said inventions, without further authorization from us, any and all benefits, including the right of priority provided by any and all treaties, conventions, or agreements.

We hereby consent that a copy of this assignment shall be deemed a full legal and formal equivalent of any document which may be required in any country in proof of the right of Micron Technology, Inc. to apply for patent or other form of protection for said inventions and to claim the aforesaid benefit of the right of priority.

We request that any and all patents for said inventions be issued to Micron Technology, Inc. in the United States and in all countries foreign to the United States, or to such nominees as Micron Technology, Inc. may designate.

We agree that, when requested, we shall, without charge to Micron Technology, Inc. but at its expense, sign all papers, and do all acts which may be necessary, desirable or convenient in connection with said applications, patents, or other forms of protection.

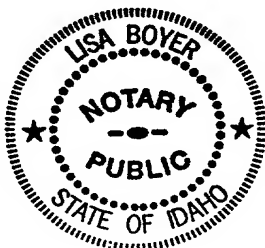

Sam Yang

Date: 5/26/00

United States of America)
State Idaho)ss.:
County Ada)

On this 26 day of May, 2000, before me personally came Sam Yang, to me known to be the individual described in and who executed the foregoing instrument, and acknowledged execution of the same.


Notary Public



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

ASSIGNMENT AND AGREEMENT

Signature Page for Second Inventor

Date:

6/1/2000

Dan Gealy
Dan Gealy

United States of America)

State Idaho)ss.:

County Ada)

On this 1 day of June, 2000, before me
personally came Dan Gealy, to me known to be the
individual described in and who executed the foregoing instrument, and acknowledged
execution of the same.

Lisa Boyer
Notary Public

